Document Number: A2G35S160-01S
Rev. 0, 5/2016

RF Power GaN Transistor

This 32 W RF power GaN transistor is designed for cellular base station applications covering the frequency range of 3400 to 3600 MHz.

This part is characterized and performance is guaranteed for applications operating in the 3400 to 3600 MHz band. There is no guarantee of performance when this part is used in applications designed outside of these frequencies.

3500 MHz

- Typical Single-Carrier W-CDMA Performance: V_{DD} = 48 Vdc, I_{DQ} = 190 mA, P_{out} = 32 W Avg., Input Signal PAR = 9.9 dB @ 0.01% Probability on CCDF.

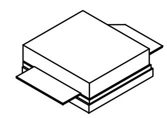
Frequency	G_{ps} (dB)	η_D (%)	Output PAR (dB)	ACPR (dBc)	IRL (dB)
3400 MHz	15.6	37.2	7.0	–33.6	–16
3500 MHz	15.7	36.7	7.2	–34.1	–16
3600 MHz	15.9	38.9	7.2	–33.2	–13

Features

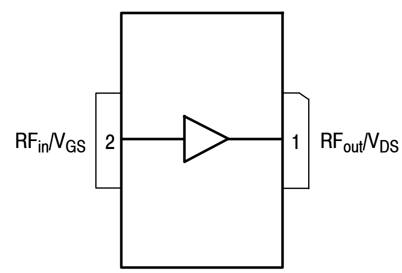
- High Terminal Impedances for Optimal Broadband Performance
- Designed for Digital Predistortion Error Correction Systems
- Optimized for Doherty Applications

A2G35S160-01SR3

3400–3600 MHz, 32 W AVG., 48 V AIRFAST RF POWER GaN TRANSISTOR



NI-400S-2S



(Top View)

Figure 1. Pin Connections

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	125	Vdc
Gate-Source Voltage	V_{GS}	–8, 0	Vdc
Operating Voltage	V_{DD}	0 to +55	Vdc
Maximum Forward Gate Current @ T_C = 25°C	I_{GMAX}	19	mA
Storage Temperature Range	T_{stg}	–65 to +150	°C
Case Operating Temperature Range	T_C	–55 to +150	°C
Operating Junction Temperature Range	T_J	–55 to +225	°C
Absolute Maximum Junction Temperature (1)	T_{MAX}	275	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance by Infrared Measurement, Active Die Surface-to-Case Case Temperature 76°C, P_D = 66 W	$R_{\theta JC}$ (IR)	1.9 (2)	°C/W
Thermal Resistance by Finite Element Analysis, Junction-to-Case Case Temperature 85°C, P_D = 65 W	$R_{\theta JC}$ (FEA)	2.5 (3)	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1A
Machine Model (per EIA/JESD22-A115)	A
Charge Device Model (per JESD22-C101)	IV

Table 4. Electrical Characteristics (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage (V_{GS} = –8 Vdc, I_D = 18.9 mAdc)	$V_{(BR)DSS}$	150	—	—	Vdc
On Characteristics					
Gate Threshold Voltage (V_{DS} = 10 Vdc, I_D = 18.9 mAdc)	$V_{GS(th)}$	–3.8	–3.1	–2.3	Vdc
Gate Quiescent Voltage (V_{DD} = 48 Vdc, I_D = 190 mAdc, Measured in Functional Test)	$V_{GS(Q)}$	–3.6	–2.6	–2.3	Vdc
Gate-Source Leakage Current (V_{DS} = 0 Vdc, V_{GS} = –5 Vdc)	I_{GSS}	–5.9	—	—	mAdc

1. Functional operation above 225°C has not been characterized and is not implied. Operation at T_{MAX} (275°C) reduces median time to failure by an order of magnitude; operation beyond T_{MAX} could cause permanent damage.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers.* Go to http://www.nxp.com/RF and search for AN1955.
3. $R_{\theta JC}$ (FEA) must be used for purposes related to reliability and limitations on maximum junction temperature. MTTF may be estimated by the expression MTTF (hours) = $10^{[A + B/(T + 273)]}$, where *T* is the junction temperature in degrees Celsius, *A* = –8.44 and *B* = 7210.

(continued)

Table 4. Electrical Characteristics (T_A = 25°C unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
Functional Tests (1) (In Freescale Test Fixture, 50 ohm system) V_{DD} = 48 Vdc, I_{DQ} = 190 mA, P_{out} = 32 W Avg., f = 3500 MHz, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 9.9 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ ±5 MHz Offset. **[See note on correct biasing sequence.]**					
Power Gain	G_{ps}	13.5	15.7	18.0	dB
Drain Efficiency	η_D	31.6	36.7	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	6.6	7.2	—	dB
Adjacent Channel Power Ratio	ACPR	—	–34.1	–31.8	dBc
Input Return Loss	IRL	—	–16	–8	dB
Load Mismatch (In Freescale Test Fixture, 50 ohm system) I_{DQ} = 190 mA, f = 3500 MHz, 12 μsec(on), 10% Duty Cycle					
VSWR 10:1 at 55 Vdc, 153 W Pulsed CW Output Power (3 dB Input Overdrive from 126 W Pulsed CW Rated Power)	No Device Degradation				
Typical Performance (In Freescale Test Fixture, 50 ohm system) V_{DD} = 48 Vdc, I_{DQ} = 190 mA, 3400–3600 MHz Bandwidth					
P_{out} @ 1 dB Compression Point, CW	P1dB	—	126	—	W
P_{out} @ 3 dB Compression Point (2)	P3dB	—	162	—	W
AM/PM (Maximum value measured at the P3dB compression point across the 3400–3600 MHz bandwidth)	Φ	—	–15.6	—	°
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW_{res}	—	110	—	MHz
Gain Flatness in 200 MHz Bandwidth @ P_{out} = 32 W Avg.	G_F	—	0.5	—	dB
Gain Variation over Temperature (–30°C to +85°C)	ΔG	—	0.02	—	dB/°C
Output Power Variation over Temperature (–30°C to +85°C)	ΔP1dB	—	0.01	—	dB/°C

Table 5. Ordering Information

Device	Tape and Reel Information	Package
A2G35S160-01SR3	R3 Suffix = 250 Units, 32 mm Tape Width, 13-inch Reel	NI-400S-2S

1. Part internally input matched.
2. P3dB = P_{avg} + 7.0 dB where P_{avg} is the average output power measured using an unclipped W-CDMA single-carrier input signal where output PAR is compressed to 7.0 dB @ 0.01% probability on CCDF.

NOTE: Correct Biasing Sequence for GaN Depletion Mode Transistors

Turning the device ON

1. Set V_{GS} to the pinch-off (V_P) voltage, typically –5 V
2. Turn on V_{DS} to nominal supply voltage (50 V)
3. Increase V_{GS} until I_{DS} current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce V_{GS} down to V_P, typically –5 V
3. Reduce V_{DS} down to 0 V (Adequate time must be allowed for V_{DS} to reduce to 0 V to prevent severe damage to device.)
4. Turn off V_{GS}

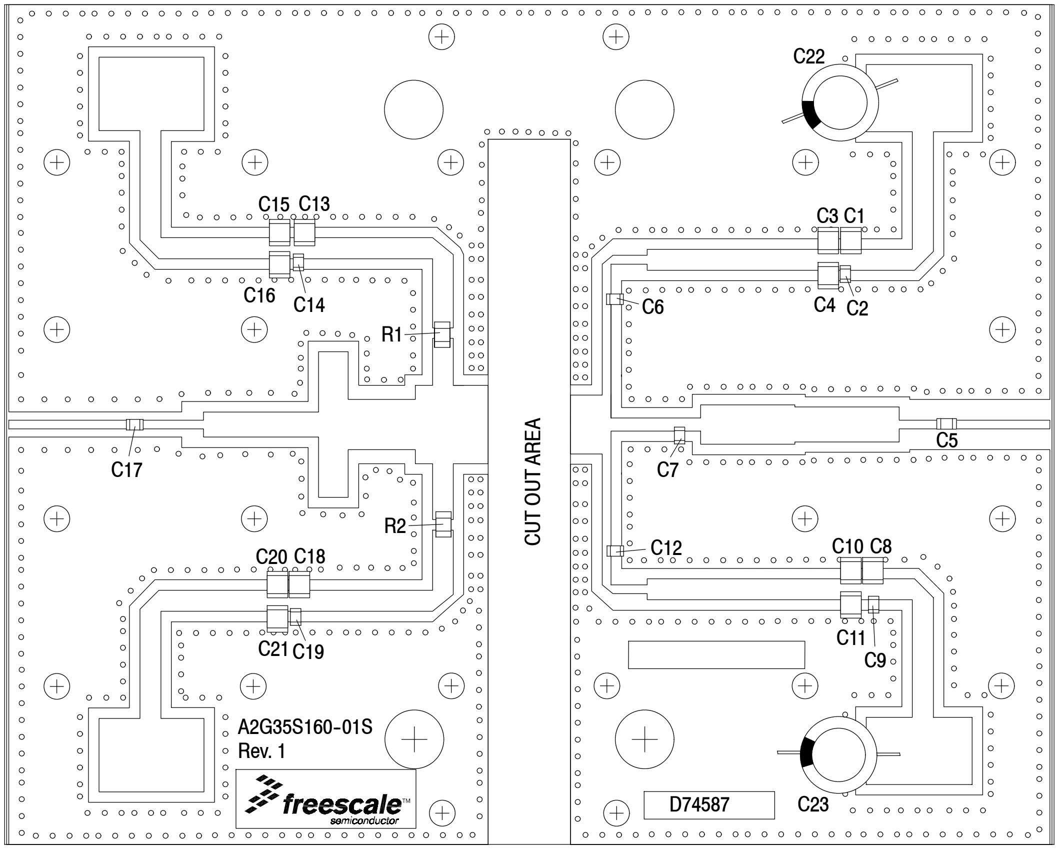


Figure 2. A2G35S160-01SR3 Test Circuit Component Layout

Table 6. A2G35S160-01SR3 Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C8, C13, C18	0.022 μF Chip Capacitors	GRM31MR72A223KA01L	Murata
C2, C9, C14, C19	1 nF Chip Capacitors	GRM1885C2A102JA01D	Murata
C3, C10, C15, C20	1 μF Chip Capacitors	GRM31CR72A105KA01L	Murata
C4, C11, C16, C21	10 μF Chip Capacitors	GRM32ER61H106KA12L	Murata
C5, C17	12 pF Chip Capacitors	GQM1875C2E120FB12D	Murata
C6, C12	15 pF Chip Capacitors	GQM1875C2E150JB12D	Murata
C7	0.6 pF Chip Capacitor	ATC600F0R6BW250XT	ATC
C22, C23	330 μF, 63 V Electrolytic Capacitors	MCRH63V337M13X21-RH	Multicomp
R1, R2	5.60 Ω, 1/4 W Chip Resistors	CRCW12065R60FKEA	Vishay
PCB	Rogers RO4350B, 0.023″, ε_r = 3.66	D74587	MTL

TYPICAL CHARACTERISTICS — 3400–3600 MHz

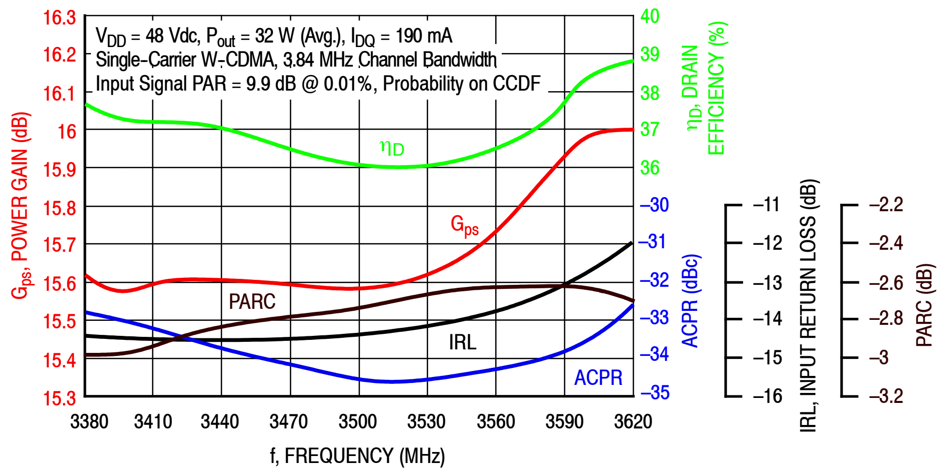


Figure 3. Single-Carrier Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @ P_{out} = 32 Watts Avg.

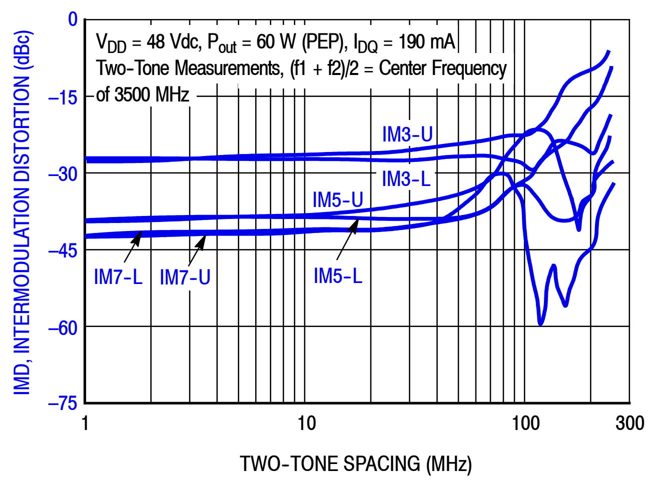


Figure 4. Intermodulation Distortion Products versus Two-Tone Spacing

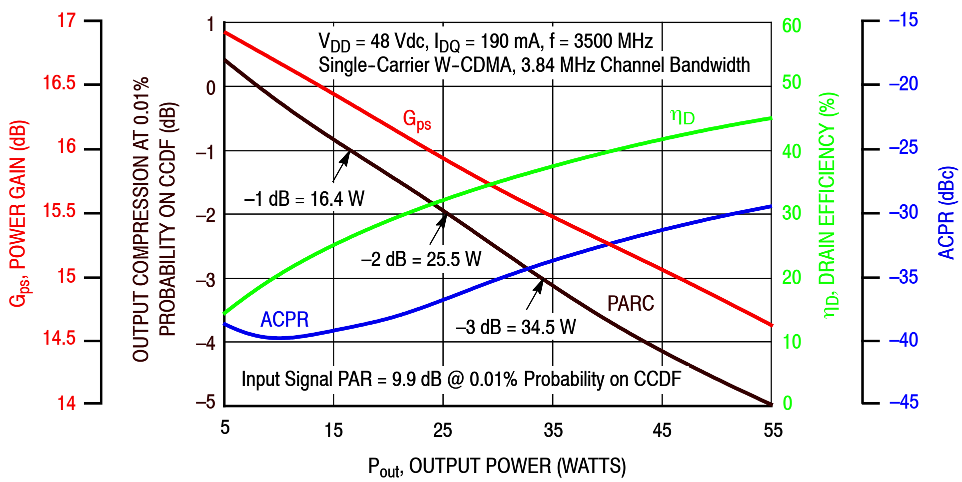


Figure 5. Output Peak-to-Average Ratio Compression (PARC) versus Output Power

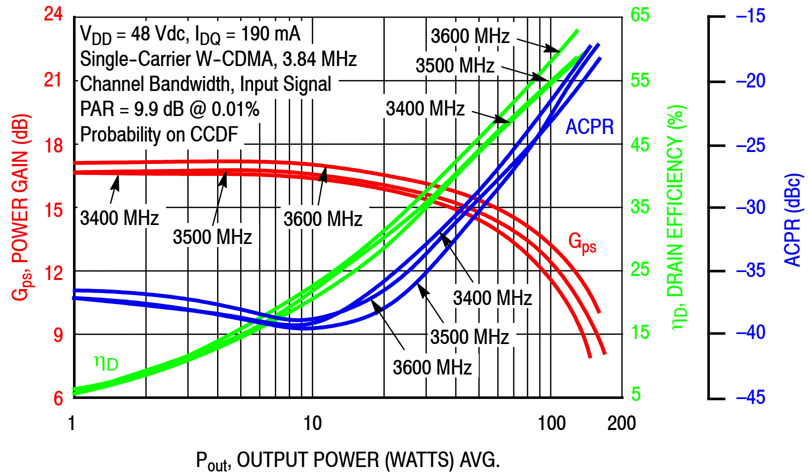


Figure 6. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power

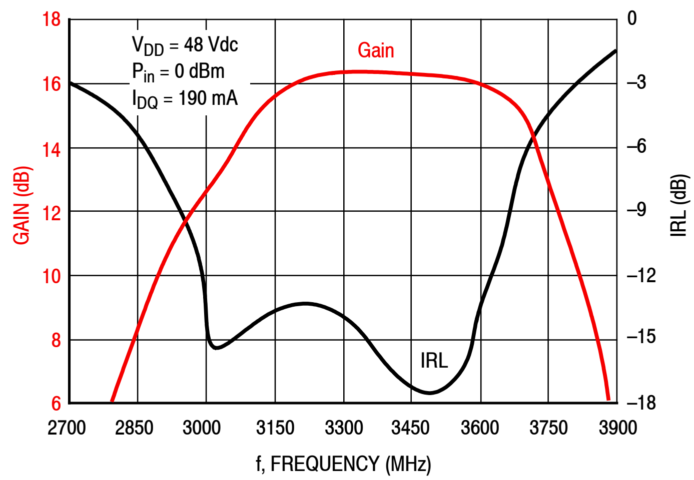
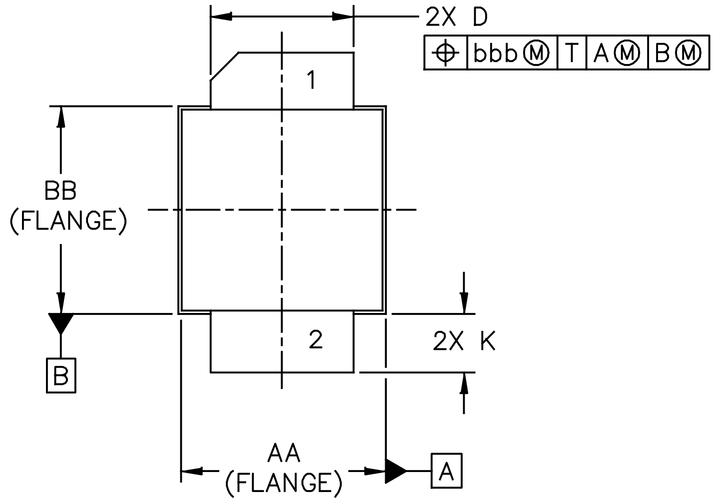
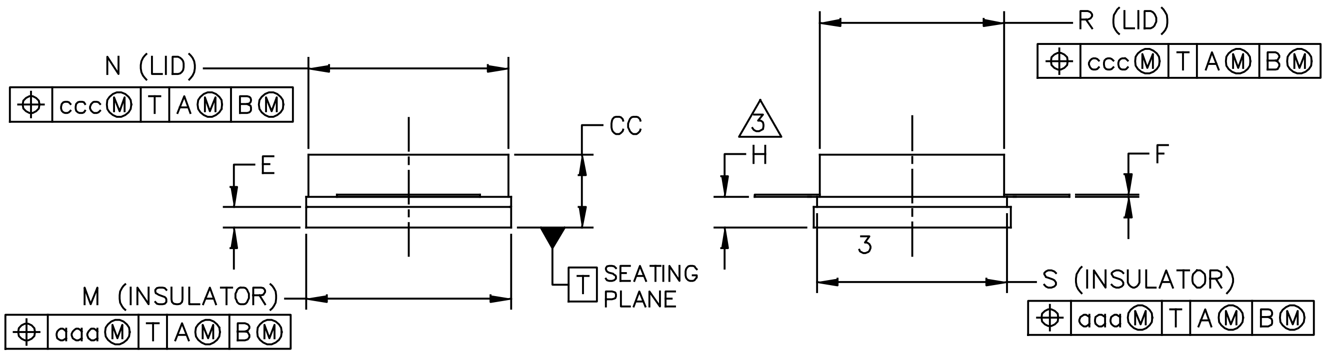


Figure 7. Broadband Frequency Response

PACKAGE DIMENSIONS





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NOTES:

1. CONTROLLING DIMENSION: INCH

2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.

3. DIMENSION H IS MEASURED .030 INCH (0.762 MM) AWAY FROM THE FLANGE TO CLEAR THE EPOXY FLOW OUT REGION PARALLEL TO DATUM B.

4. INPUT & OUTPUT LEADS (PIN 1 & 2) MAY HAVE SMALL FEATURES SUCH AS SQUARE HOLES OR NOTCHES FOR MANUFACTURING CONVENIENCE.

DIM	INCH MIN	INCH MAX	MILLIMETER MIN	MILLIMETER MAX	DIM	INCH MIN	INCH MAX	MILLIMETER MIN	MILLIMETER MAX
AA	.395	.405	10.03	10.29	aaa	.005		0.13	
BB	.382	.388	9.70	9.86	bbb	.010		0.25	
CC	.125	.163	3.18	4.14	ccc	.015		0.38	
D	.275	.285	6.98	7.24					
E	.035	.045	0.89	1.14					
F	.004	.006	0.10	0.15					
H	.057	.067	1.45	1.70					
K	.0995	.1295	2.53	3.29					
M	.395	.405	10.03	10.29					
N	.385	.395	9.78	10.03					
R	.355	.365	9.02	9.27					
S	.365	.375	9.27	9.53					

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PRODUCT DOCUMENTATION, SOFTWARE AND TOOLS

Refer to the following resources to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- RF High Power Model
- .s2p File

Development Tools

- Printed Circuit Boards

To Download Resources Specific to a Given Part Number:

1. Go to http://www.nxp.com/RF
2. Search by part number
3. Click part number link
4. Choose the desired resource from the drop down menu

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	May 2016	• Initial Release of Data Sheet

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Document Number: A2G35S160-01S
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